

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-092122
(43)Date of publication of application : 06.04.2001

(51)Int.CI. G03F 7/004
G03F 7/11
H01L 21/027

(21)Application number : 11-265408
(22)Date of filing : 20.09.1999

(71)Applicant : TOKYO OHKA KOGYO CO LTD
(72)Inventor : SAKAMOTO YOSHIKANE
SHIBUYA TATSUHIKO
WAKIYA KAZUMASA
IGUCHI ETSUKO
OMORI KATSUMI
YAMADA TOMOTAKA
HAGIWARA YOSHIO

(54) COMPOSITION FOR FORMING ANTIREFLECTION FILM AND RESIST PATTERN FORMING METHOD

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a composition for forming an antireflection film having a higher dry etching rate than a photoresist.

SOLUTION: The composition contains (A) at least one compound selected from a compound of the formula $\text{Si}(\text{OR1})\text{a}(\text{OR2})\text{b}(\text{RO3})\text{c}(\text{OR4})\text{d}$ (where R1-R4 are each a 1-4C alkyl or phenyl), a compound of the formula $\text{R5Si}(\text{OR6})\text{e}(\text{OR7})\text{f}(\text{OR8})\text{g}$ (where R5 is H, a 1-4C alkyl or phenyl and R6-R8 are each a 1-3C alkyl or phenyl) and a compound of the formula $\text{R9R10Si}(\text{OR11})\text{h}(\text{OR12})\text{i}$ (where R9 and R10 are each H, a 1-4C alkyl or phenyl and R11 and R12 are each a 1-3C alkyl or phenyl), and (B) at least one highly light absorbing material having a substituent capable of condensing with the component A in its structure.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]